

## N-Channel 100-V (D-S) MOSFET

**PRODUCT SUMMARY**

$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)	$Q_g$ (Typ)
100	0.0088 at $V_{GS} = 10$ V	90 <sup>d</sup>	97

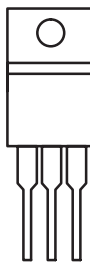
**FEATURES**

- TrenchFET<sup>®</sup> Power MOSFET
- 175 °C Junction Temperature
- 100 %  $R_g$  and UIS Tested


**RoHS**  
COMPLIANT

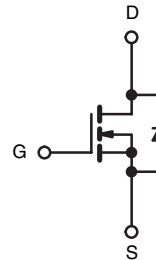
**APPLICATIONS**

- Power Supply
  - Secondary Synchronous Rectification
- Industrial
- Primary Switch

**TO-220AB**


G D S

Top View

**Ordering Information:** SUP90N10-8m8P-E3 (Lead (Pb)-free)


N-Channel MOSFET

**ABSOLUTE MAXIMUM RATINGS**  $T_C = 25$  °C, unless otherwise noted

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	$V_{DS}$	100	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current ( $T_J = 175$ °C)	$I_D$	$T_C = 25$ °C	90 <sup>d</sup>	A
		$T_C = 70$ °C	90 <sup>d</sup>	
Pulsed Drain Current	$I_{DM}$	240		
Avalanche Current	$I_{AS}$	60		
Single Avalanche Energy <sup>a</sup>	$E_{AS}$	180	mJ	
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_C = 25$ °C	300 <sup>b</sup>	W
		$T_A = 25$ °C <sup>c</sup>	3.75	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 175	°C	

**THERMAL RESISTANCE RATINGS**

Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) <sup>c</sup>	$R_{thJA}$	40	°C/W
Junction-to-Case (Drain)	$R_{thJC}$	0.5	

Notes:

- Duty cycle  $\leq 1$  %.
- See SOA curve for voltage derating.
- When Mounted on 1" square PCB (FR-4 material).
- Package limited.

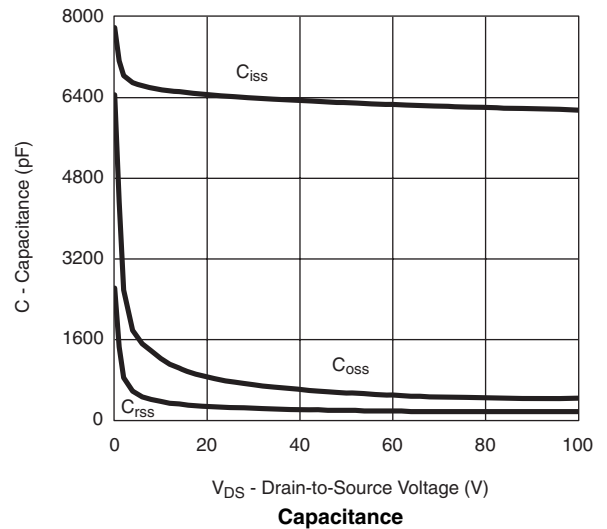
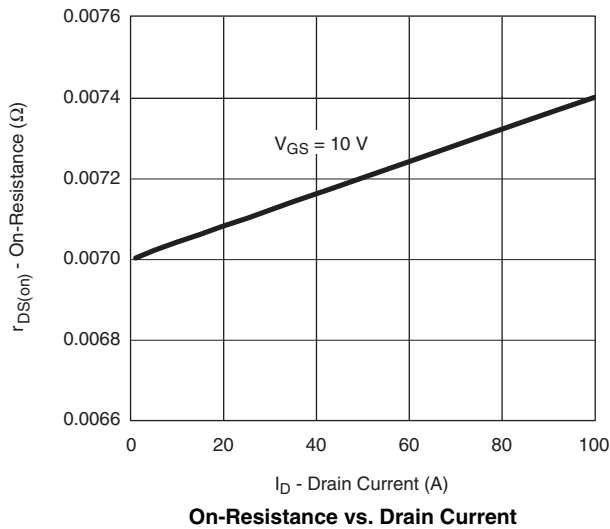
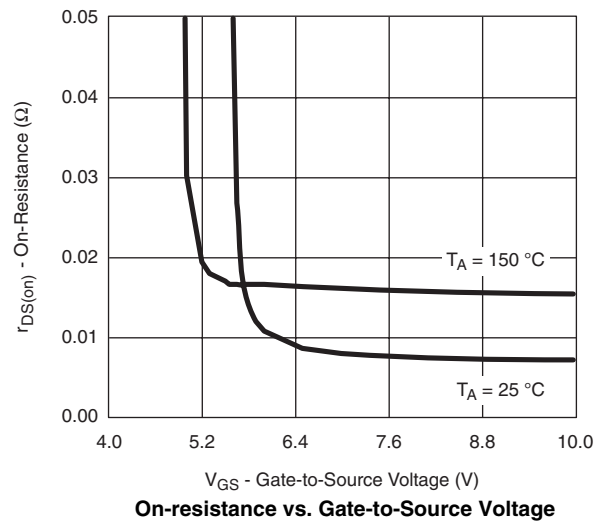
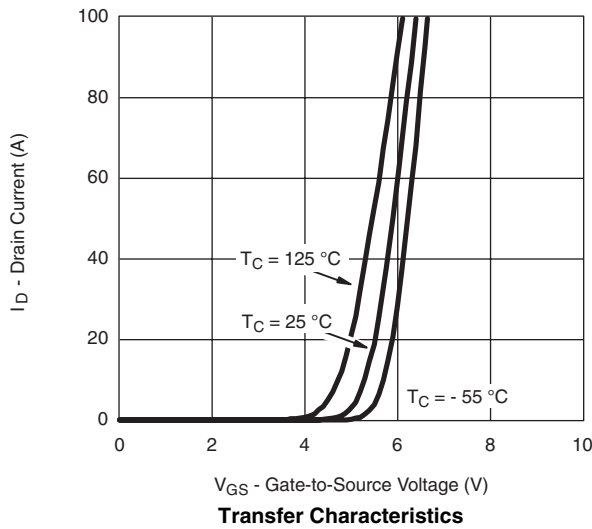
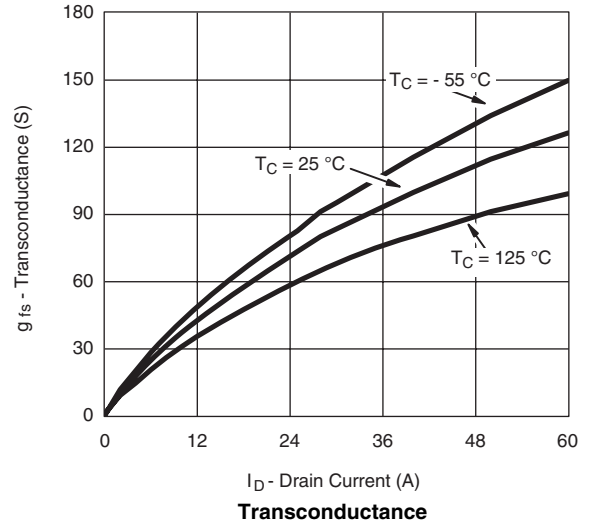
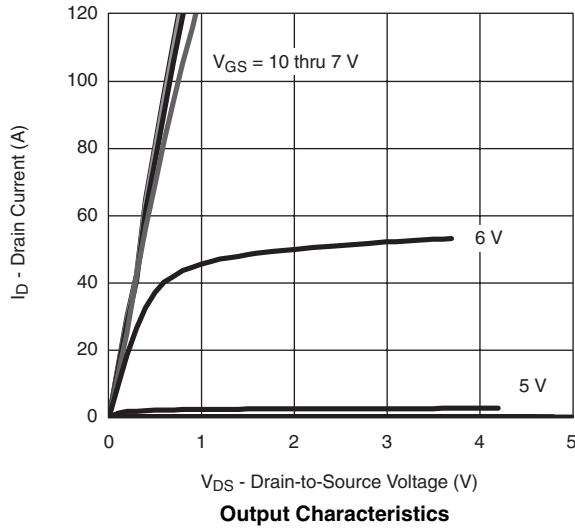
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{DS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.5		4.5	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 250$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$			250	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 10\text{ V}$	70			A
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		0.00725	0.0088	$\Omega$
		$V_{GS} = 10\text{ V}, I_D = 20\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.0137	0.0184	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 20\text{ A}$		62		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 50\text{ V}, f = 1\text{ MHz}$		6290		$\mu\text{F}$
Output Capacitance	$C_{oss}$			535		
Reverse Transfer Capacitance	$C_{rss}$			182		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 85\text{ A}$		97	150	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			32		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			25		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		1.4	2.8	$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 0.588\text{ }\Omega$ $I_D \approx 85\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		23	35	ns
Rise Time <sup>c</sup>	$t_r$			17	26	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			34	52	
Fall Time <sup>c</sup>	$t_f$			9	18	
<b>Source-Drain Diode Ratings and Characteristics</b> ( $T_C = 25\text{ }^\circ\text{C}$ ) <sup>b</sup>						
Continuous Current	$I_S$				85	A
Pulsed Current	$I_{SM}$				240	
Forward Voltage <sup>a</sup>	$V_{SD}$	$I_F = 30\text{ A}, V_{GS} = 0\text{ V}$		0.85	1.5	V
Reverse Recovery Time	$t_{rr}$	$I_F = 75\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		61	100	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			3.0	4.5	A
Reverse Recovery Charge	$Q_{rr}$				91	130

Notes:

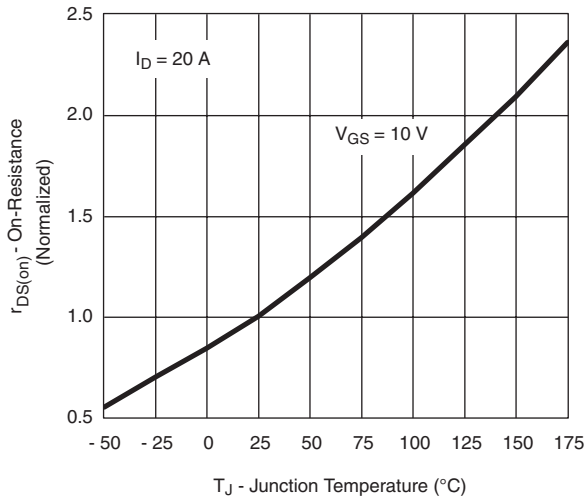
- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

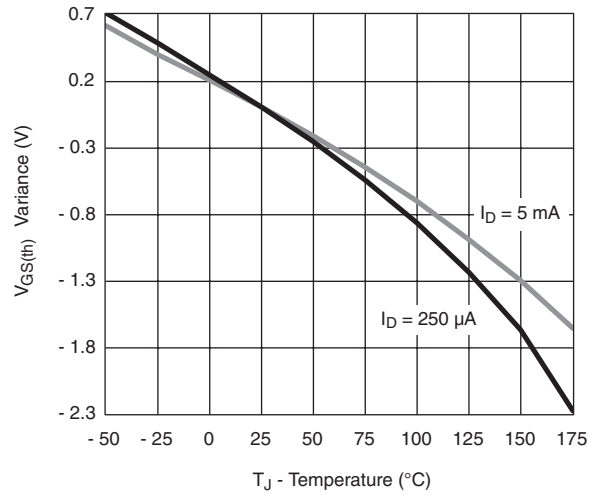
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



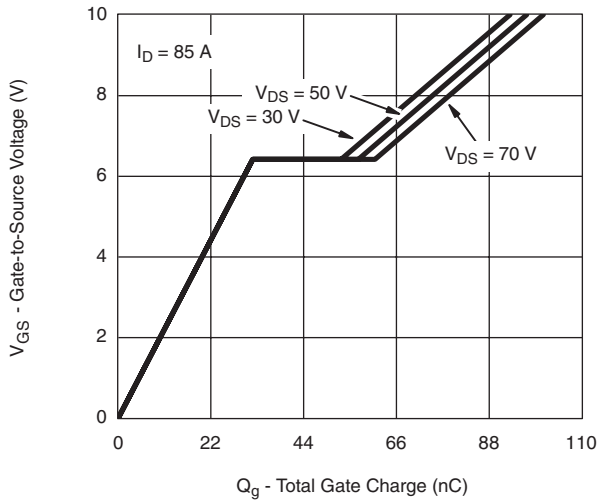
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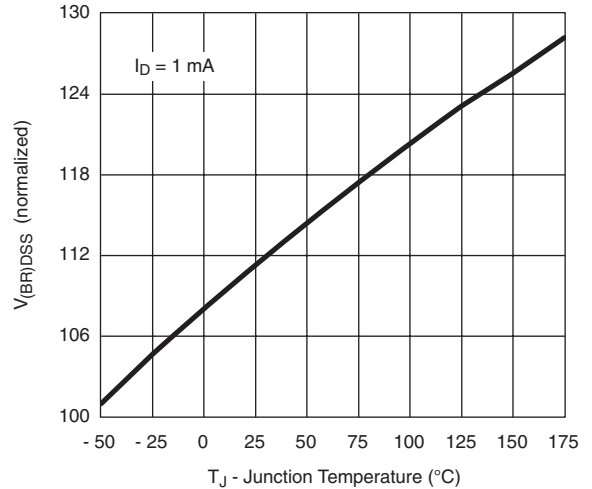
**On-Resistance vs. Junction Temperature**



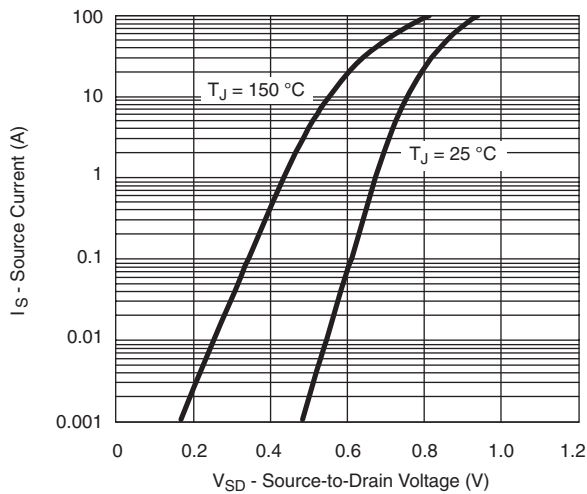
**Threshold Voltage**



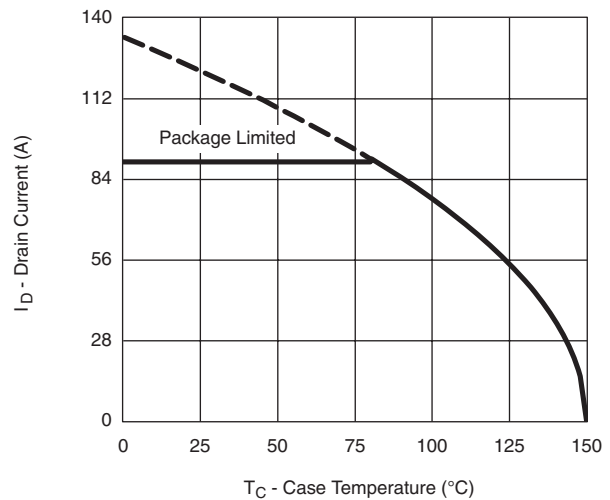
**Gate Charge**



**Drain Source Breakdown vs. Junction Temperature**

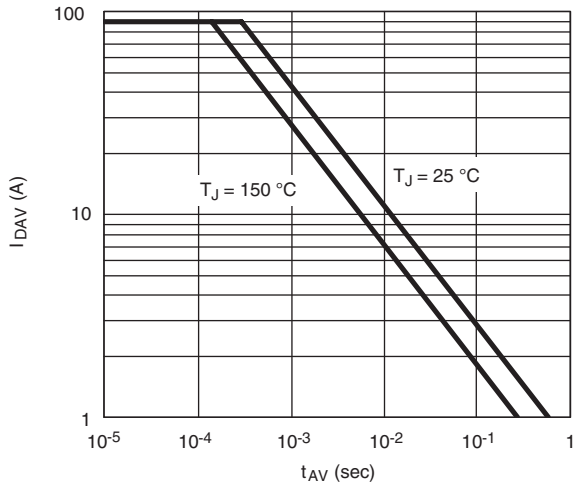


**Source-Drain Diode Forward Voltage**

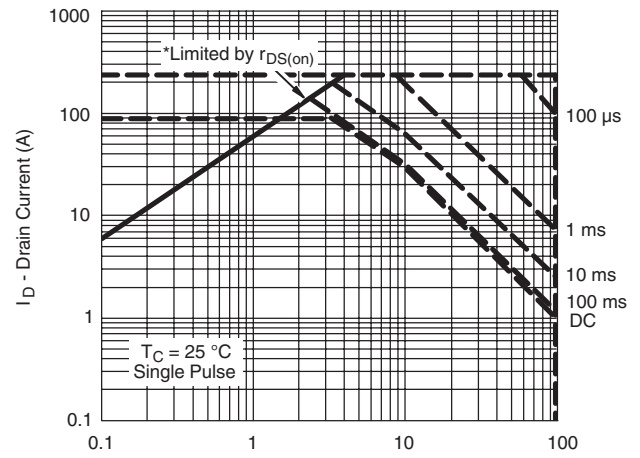


**Maximum Drain Current vs. Case Temperature**

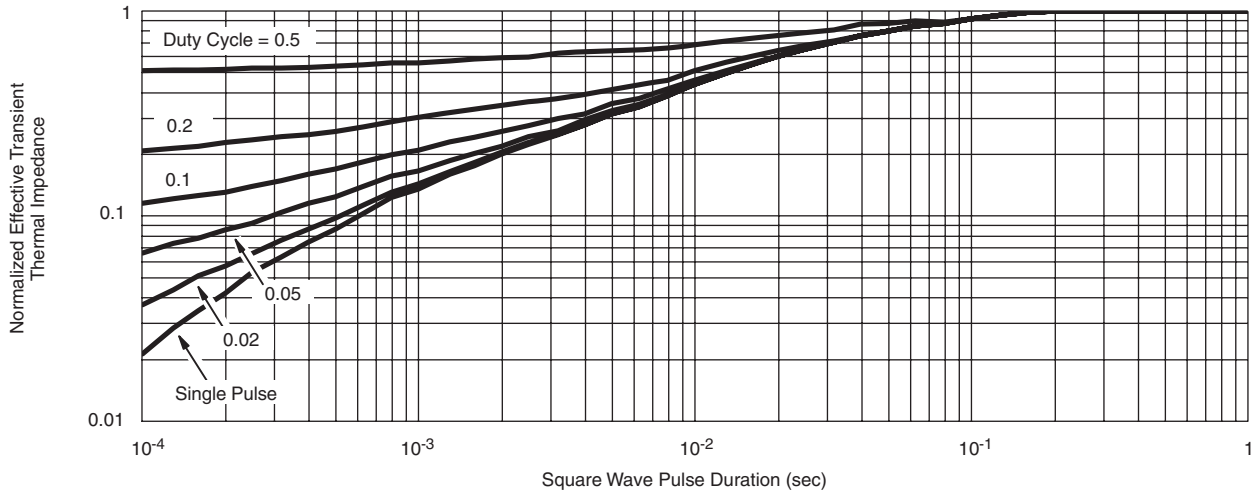
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**Single Pulse Avalanche Current Capability vs. Time**



**Safe Operating Area**  
 $V_{GS} > \text{minimum } V_{GS} \text{ at which } r_{DS(on)} \text{ is specified}$



**Normalized Thermal Transient Impedance, Junction-to-Case**

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